RÃ¼diger Quay

List of Publications by Year
in descending order

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284	3,337	218592	289141
papers	citations	26 h-index	40 g-index

292	292	292	2368
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Wideband E/W-Band Low-Noise Amplifier MMIC in a 70-nm Gate-Length GaN HEMT Technology. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1367-1376.	2.9	17
2	16-Way Ka-Band Power Combiner Using Novel Waveguide Transitions. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 3074-3086.	2.9	5
3	Broadband 100-W Ka-Band SSPA Based on GaN Power Amplifiers. IEEE Microwave and Wireless Components Letters, 2022, 32, 708-711.	2.0	7
4	Harmonic-Injection Doherty Power Amplifiers with a High Small-Signal Gain. , 2022, , .		0
5	A 41.5 dBm Broadband AlGaN/GaN HEMT Balanced Power Amplifier at K-Band. , 2022, , .		2
6	Bandwidth and Power Back-Off Performances of a Class-E_M/F₃Power Amplifier. , 2022, , .		0
7	PCB-Embedded GaN-on-Si Half-Bridge and Driver ICs With On-Package Gate and DC-Link Capacitors. IEEE Transactions on Power Electronics, 2021, 36, 83-86.	5.4	19
8	Monolithic Integrated AlGaN/GaN Power Converter Topologies on Highâ€Voltage AlN/GaN Superlattice Buffer. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000404.	0.8	12
9	Low-Power Differential Input to Single-Ended Output GaN RF-DAC for RF-Signal Generation. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 1646-1653.	2.9	1
10	Limitations and Implementation Strategies of Interstage Matching in a 6-W, 28â€“38-GHz GaN Power Amplifier MMIC. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 2541-2553.	2.9	18
11	A GaN-Based Active Diode Circuit for Low-Loss Rectification. , 2021, , .		1
12	Polarization induced interface and electron sheet charges of pseudomorphic ScAlN/GaN, GaAlN/GaN, InAlN/GaN, and InAlN/InN heterostructures. Journal of Applied Physics, 2021, 129, .	1.1	30
13	Harmonic-Injection Class-E_M/F_n Power Amplifier With Finite DC-Feed Inductance and Isolation Circuit. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 3319-3334.	2.9	9
14	Broadband 400-GHz InGaAs mHEMT Transmitter and Receiver S-MMICs. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 660-675.	2.0	10
15	A 28-90-GHz GaN Power Amplifier MMIC Using an Integrated f_T-Doubler Topology. , 2021, , .		1
16	Building Blocks for GaN Power Integration. IEEE Access, 2021, 9, 163122-163137.	2.6	13
17	Deep-level characterization of GaN-on-GaN current aperture vertical electron transistors. , 2021, , .		5
18	Metalâ€Organic Chemical Vapor Deposition of Aluminum Scandium Nitride. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900535.	1.2	54

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19	Optimization of Metalâ€Organic Chemical Vapor Deposition Regrown nâ€GaN. Physica Status Solidi (B): Basic Research, 2020, 257, 1900436.	0.7	6
20	A 600V p-GaN Gate HEMT with Intrinsic Freewheeling Schottky-Diode in a GaN Power IC with Bootstrapped Driver and Sensors. , 2020, , .		3
21	First Demonstration of G-Band Broadband GaN Power Amplifier MMICs Operating Beyond 200 GHz. , 2020, , .		8
22	A GaN-based Current Sense Amplifier for GaN HEMTs with Integrated Current Shunts. , 2020, , .		5
23	Si-Substrate Removal for AlGaN/GaN Devices on PCB Carriers. , 2020, , .		3
24	A Novel 32-Gb/s 5.6-Vpp Digital-to-Analog Converter in 100 nm GaN Technology for 5G Signal Generation. , 2020, , .		1
25	Large-Area Lateral AlGaN/GaN-on-Si Field-Effect Rectifier With Low Turn-On Voltage. IEEE Electron Device Letters, 2020, 41, 993-996.	2.2	20
26	Failure Analysis of 100 nm AlGaN/GaN HEMTs Stressed under On- and Off-State Stress. , 2020, , .		1
27	Study of Power Amplifier Harmonic Output Termination for two AlGaN/GaN Technologies at K-/Ka-Band. , 2020, , .		0
28	Adaptive low-temperature covalent bonding of III-nitride thin films by extremely thin water interlayers. Applied Physics Letters, 2019, 114, 252103.	1.5	9
29	High-Power (>2 W) E-Band PA MMIC Based on High Efficiency GaN-HEMTs with Optimized Buffer. , 2019, , .		17
30	Integrated 2-b Riemann Pump RF-DAC in GaN Technology for 5G Base Stations. , 2019, , .		4
31	Integrated Current Sensing in GaN Power ICs. , 2019, , .		11
32	Consistent Modelling of I-V and C-V Behaviour of GaN HEMTs in Presence of Trapping. , 2019, , .		4
33	High-Q Anti-Series AlGaN/GaN High Electron-Mobility Varactor. , 2019, , .		3
34	Design, Analysis and Evaluation of a Broadband High-Power Amplifier for Ka-Band Frequencies. , 2019, , .		20
35	Highly linear 90-170 GHz SPDT Switch with High Isolation for Fully Integrated InP Transceivers. , 2019, , .		9
36	190-GHz G-Band GaN Amplifier MMICs with 40GHz of Bandwidth. , 2019, , .		4

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37	D-Band and G-Band High-Performance GaN Power Amplifier MMICs. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 5080-5089.	2.9	43
38	Millimeter-Wave Single-Pole Double-Throw Switches Based on a 100-nm Gate-Length AlGaN/GaN-HEMT Technology. , 2019, , .		16
39	Large-Signal Modeling of a Scalable High-${Q}$ AlGaN/GaN High Electron-Mobility Varactor. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 922-927.	2.9	4
40	Epitaxial growth optimization of AlGaN/GaN high electron mobility transistor structures on 3C-SiC/Si. Journal of Applied Physics, 2019, 125, .	1.1	15
41	AlGaN/GaN High Electron-mobility Varactors on Silicon Substrate. , 2019, , .		0
42	High-Power-Density AlGaN/GaN Technology for 100-V Operation at L-Band Frequencies. , 2019, , .		5
43	Asymmetrical Substrate-Biasing Effects at up to 350V Operation of Symmetrical Monolithic Normally-Off GaN-on-Si Half-Bridges. , 2019, , .		5
44	Deep Submicron III-N HEMTs â€“ Technological Development and Reliability. , 2019, , .		3
45	A Pseudo-Complementary GaN-Based Gate Driver with Reduced Static Losses. , 2019, , .		3
46	3 GHz RF measurements of AlGaN/GaN transistors transferred from silicon substrates onto single crystalline diamond. AIP Advances, 2019, 9, 125106.	0.6	5
47	Highâ€Power Microwave GaN/AlGaN HEMTs and MMICs on SiC and Silicon Substrates for Modern Radio Communication. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700655.	0.8	16
48	A 5 W AlGaN/GaN power amplifier MMIC for 25â€“27 GHz downlink applications. , 2018, , .		9
49	Two Q-band power amplifier MMICs in 100 nm AlGaN/GaN HEMT technology. , 2018, , .		2
50	W-band SPDT switches in planar and tri-gate 100-nm gate-length GaN-HEMT technology. , 2018, , .		20
51	Suppression of Iron Memory Effect in GaN Epitaxial Layers. Physica Status Solidi (B): Basic Research, 2018, 255, 1700377.	0.7	24
52	Voltage- and Temperature-Dependent Degradation of AlN/GaN High Electron Mobility Transistors. , 2018, , .		3
53	Multi-Stage Cascode in High-Voltage AlGaN/GaN-on-Si Technology. , 2018, , .		6
54	Investigation of High-Efficiency Hybrid Power Combining for Ka-Band Frequencies. , 2018, , .		1

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55	Full W-Band GaN Power Amplifier MMICs Using a Novel Type of Broadband Radial Stub. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 5664-5675.	2.9	19
56	A Novel Type of Broadband Radial Stub. , 2018, , .		1
57	High-Power Asymmetrical Three-Way GaN Doherty Power Amplifier at C-Band Frequencies. , 2018, , .		0
58	State Dependency, Low-Frequency Dispersion, and Thermal Effects in Microwave III-V HEMTs. , 2018, , .		1
59	Broadband GaN-Based Power Amplifier MMIC and Module for V-Band Measurement Applications. , 2018, , .		6
60	Dynamic Load Modulated Low-Voltage GaN PA Using Novel Low-Loss GaN Varactors. , 2018, , .		1
61	High-Power Asymmetrical Three-Way GaN Doherty Power Amplifier at C-Band Frequencies. , 2018, , .		0
62	Instabilities by Parasitic Substrate-Loop of GaN-on-Si HEMTs in Half-Bridges. , 2018, , .		1
63	RF-Noise Modeling of InGaAs Metamorphic HEMTs and MOSFETs. , 2018, , .		2
64	Comparison of reliability of 100â€¯nm AlGaN/GaN HEMTs with T-gate and SAG-gate technology. Microelectronics Reliability, 2018, 88-90, 385-388.	0.9	5
65	Riemann-Pump based RF-Power DACs in GaN Technology for 5G Base Stations. , 2018, , .		5
66	Investigations of Active Antenna Doherty Power Amplifier Modules Under Beam-Steering Mismatch. IEEE Microwave and Wireless Components Letters, 2018, 28, 930-932.	2.0	10
67	First Full W-Band GaN Power Amplifier MMICs with Novel Broadband Radial Stubs and 50 GHz of Bandwidth. , 2018, , .		3
68	A Beyond 110 GHz GaN Cascode Low-Noise Amplifier with 20.3 dBm Output Power. , 2018, , .		17
69	Monolithically integrated power circuits in highâ€voltage GaNâ€onâ€Si heterojunction technology. IET Power Electronics, 2018, 11, 681-688.	1.5	35
70	mm-Wave operation of AlN/GaN-devices and MMICs at V- & W-band. , 2018, , .		10
71	Transfer of AlGaN/GaN RF-devices onto diamond substrates via van der Waals bonding. International Journal of Microwave and Wireless Technologies, 2018, 10, 666-673.	1.5	20
72	Low-frequency dispersion and state dependency in modem microwave III-V HEMTs. , 2018, , .		2

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73	Performance evaluation of commercial GaN RF HEMTs as hybrid topology power switches. , 2018, , .		0
74	X-band GaN high power amplifier with integrated power switch for airborne applications. , 2018, , .		1
75	Enhancement of the Broadband Efficiency of a Class-J Power Amplifier With Varactor-based Dynamic Load Modulation. IEEE Microwave and Wireless Components Letters, 2017, 27, 180-182.	2.0	21
76	Demonstration of an RF front-end based on GaN HEMT technology. , 2017, , .		0
77	Noise degradation of cascodes in broadband power amplifiers. , 2017, , .		1
78	New Concept for Power Compression Improvement of GaN Cascodes in Broadband Power Amplifiers. IEEE Microwave and Wireless Components Letters, 2017, 27, 590-592.	2.0	4
79	First demonstration of W-band Tri-gate GaN-HEMT power amplifier MMIC with 30 dBm output power. , 2017, , .		11
80	Hetero-integrated GaN MMICs: Hot Islands in a (Silicon) Oceanâ€¦ , 2017, , .		3
81	Reliability of 100 nm AlGaN/GaN HEMTs for mm-wave applications. Microelectronics Reliability, 2017, 76-77, 292-297.	0.9	12
82	AlN/GaN HEMTs grown by MBE and MOCVD: Impact of Al distribution. Physica Status Solidi (B): Basic Research, 2017, 254, 1600715.	0.7	23
83	Design, Realization, and Evaluation of a Riemann Pump in GaN Technology. IEEE Microwave and Wireless Components Letters, 2017, 27, 672-674.	2.0	6
84	Substrate biasing effects in a high-voltage, monolithically-integrated half-bridge GaN-Chip. , 2017, , .		25
85	Radiation aspects and performance of GaN power converters and RFICs for airborne and space applications. , 2017, , .		0
86	Effect of substrate termination on switching loss and switching time using 600 V GaN-on-Si HEMTs with integrated gate driver in half-bridges. , 2017, , .		13
87	Operation of PCB-embedded, high-voltage multilevel-converter GaN-IC. , 2017, , .		11
88	Enhanced GaN HEMT technology for E-band power amplifier MMICs with 1W output power. , 2017, , .		15
89	A sequential power amplifier at 3.5 GHz for 5G applications. , 2017, , .		6
90	New concept to control the gain of GaN-cascodes in broadband power amplifiers. , 2017, , .		1

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91	Transfer of AlGaN/GaN RF-devices onto diamond substrates via van der Waals bonding. , 2017, , .		3
92	Group Iii-Nitride Microwave Monolithically Integrated Circuits. , 2017, , 141-201.		0
93	A GaN-Based 10.1MHz Class-F-1 300 W Continuous Wave Amplifier Targeting Industrial Power Applications. , 2016, , .		1
94	Broadband E-Band Power Amplifier MMIC Based on an AlGaN/GaN HEMT Technology with 30 dBm Output Power. , 2016, , .		13
95	Single-input GaN gate driver based on depletion-mode logic integrated with a 600 V GaN-on-Si power transistor. , 2016, , .		10
96	Soft-switching 3 MHz converter based on monolithically integrated half-bridge GaN-chip. , 2016, , .		18
97	Slew rate control of a 600 V 55 mÎ© GaN cascode. , 2016, , .		1
98	Enhancement-mode AlGaN/GaN FinFETs with high on/off performance in 100 nm gate length. , 2016, , .		5
99	Internally-packaged-matched continuous inverse class-FI wideband GaN HPA. , 2016, , .		1
100	Dual-gate HEMT parameter extraction based on 2.5D multiport simulation of passive structures. , 2016, , .		2
101	A Q-band power amplifier MMIC using 100 nm AlGaN/GaN HEMT. , 2016, , .		10
102	Multi-decade GaN feedback power amplifiers in common-source and cascode topology. , 2016, , .		3
103	GaN-based E-band power amplifier modules. , 2016, , .		9
104	Packaged AlGaN/GaN HEMT power bars with 900 W output power and high PAE at L-band. , 2016, , .		2
105	Active multi-feed satcom systems with GaN SSPA at K-band. , 2016, , .		2
106	A 40 dBm AlGaN/GaN HEMT power amplifier MMIC for SatCom applications at K-band. , 2016, , .		27
107	Performance of tri-gate AlGaN/GaN HEMTs. , 2016, , .		5
108	RF Performance of Trigate GaN HEMTs. IEEE Transactions on Electron Devices, 2016, 63, 4255-4261.	1.6	18

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109	Analysis and modeling of GaN-based multi field plate Schottky power diodes. , 2016, , .		8
110	High voltage GaN-based Schottky diodes in non-isolated LED buck converters. , 2016, , .		1
111	Linear temperature sensors in high-voltage GaN-HEMT power devices. , 2016, , .		9
112	High-Current Submicrometer Tri-Gate GaN High-Electron Mobility Transistors With Binary and Quaternary Barriers. IEEE Journal of the Electron Devices Society, 2016, 4, 1-6.	1.2	28
113	Trapping Effects at the Drain Edge in 600 V GaN-on-Si HEMTs. IEEE Transactions on Electron Devices, 2016, 63, 598-605.	1.6	11
114	A novel broadband high-power source-pull/ load-pull concept for the HF- to UHF-range. , 2015, , .		0
115	With electroluminescence microcopy towards more reliable AlGaN/GaN transistors. , 2015, , .		0
116	Monolithic integrated quasi-normally-off gate driver and 600 V GaN-on-Si HEMT. , 2015, , .		20
117	A dual-band UMTS/LTE highly power-efficient Class-ABJ Doherty GaN PA. , 2015, , .		0
118	A dual-band UMTS/LTE highly power-efficient class-ABJ Doherty GaN PA. , 2015, , .		1
119	Examples of high-speed harmonic load pull investigations of high-efficiency GaN power transistors. , 2015, , .		0
120	Microwave monolithic integrated gallium-nitride switches for low static power reconfigurable switch matrix with passive transparent state for power failure redundancy. , 2015, , .		1
121	High-gain over 30% PAE power amplifier MMICs in 100 nm GaN technology at Ka-band frequencies. , 2015, , .		12
122	A novel broadband high-power Source-Pull/ Load-Pull concept for the HF- to UHF-range. , 2015, , .		2
123	High-Gain AlGaN/GaN HEMT Single Chip E-Band Power Amplifier MMIC with 30 dBm Output Power. , 2015, , .		5
124	Broadband low-noise GaN HEMT TWAs using an active distributed drain bias circuit. , 2015, , .		4
125	Monolithic three-stage 6â€“18GHz high power amplifier with distributed interstage in GaN technology. , 2015, , .		7
126	Performance and parasitic analysis of sub-micron scaled tri-gate AlGaN/GaN HEMT design. , 2015, , .		9

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127	High-voltage stress time-dependent dispersion effects in AlGaN/GaN HEMTs. , 2015, , .		6
128	Integrated reverse-diodes for GaN-HEMT structures. , 2015, , .		26
129	Quasi-normally-off GaN gate driver for high slew-rate d-mode GaN-on-Si HEMTs. , 2015, , .		6
130	Assembly and Packaging Technologies for High-Temperature and High-Power GaN Devices. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2015, 5, 1402-1416.	1.4	55
131	High-Efficiency, High-Temperature Continuous Class-E Sub-Waveform Solution AlGaN/GaN Power Amplifier. IEEE Microwave and Wireless Components Letters, 2015, 25, 526-528.	2.0	7
132	Switching frequency modulation for GaN-based power converters. , 2015, , .		6
133	The Resistive-Reactive Class-J Power Amplifier Mode. IEEE Microwave and Wireless Components Letters, 2015, 25, 666-668.	2.0	49
134	A high-power Ka-band single-pole single-throw switch MMIC using 0.25 Âµm GaN on SiC. , 2015, , .		6
135	Degradation of 0.25 Î¼m GaN HEMTs under high temperature stress test. Microelectronics Reliability, 2015, 55, 1667-1671.	0.9	11
136	Monolithically-Integrated Mulitlevel Inverter on Lateral GaN-on-Si Technology for High-Voltage Applications. , 2015, , .		6
137	Realization of a 30-W highly efficient and linear reconfigurable dual-band power amplifier using the continuous mode approach. International Journal of Microwave and Wireless Technologies, 2014, 6, 115-128.	1.5	7
138	RF-MEMS variable matching networks and switches for multi-band and multi-mode GaN power amplifiers. International Journal of Microwave and Wireless Technologies, 2014, 6, 265-276.	1.5	0
139	Broadband 1.7â€“2.8 GHz high-efficiency (58%), high-power (43 dBm) Class-BJ GaN power amplifier including package engineering. , 2014, , .		1
140	Automatic extraction of analytical large-signal FET models with parameter estimation by function decomposition. , 2014, , .		2
141	Comparison of second-harmonic matching of AlGaN/GaN HEMTs at K-band. , 2014, , .		0
142	Reliability of GaN HEMTs with a 100 nm gate length under DC-stress tests. , 2014, , .		4
143	Broadband 1.7â€“2.8 GHz high-efficiency (58%), high-power (43 dBm) Class-BJ GaN power amplifier including package engineering. , 2014, , .		1
144	Design of GaN tri-gate HEMTs. , 2014, , .		2

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145	A microwave high-power GaN transistor with highly-integrated active digital switch-mode driver circuit. , 2014, , .		3
146	Influence of surface states on the voltage robustness of AlGaN/GaN HFET power devices. Microelectronics Reliability, 2014, 54, 2656-2661.	0.9	9
147	Characterization of AlGaN/GaN-on-Si HFETs in high-power converter applications. , 2014, , .		3
148	K-band power amplifiers in a 100 nm GaN HEMT microstrip line MMIC technology. , 2014, , .		9
149	RF-MEMS multi-mode-matching networks for GaN power transistors. International Journal of Microwave and Wireless Technologies, 2014, 6, 447-458.	1.5	3
150	High linearity active GaN-HEMT down-converter MMIC for E-band radar applications. , 2014, , .		6
151	Assembly and packaging technologies for high-temperature and high-power GaN HEMTs. , 2014, , .		9
152	The Sky's the Limit: Key Technology and Market Trends in Satellite Communications. IEEE Microwave Magazine, 2014, 15, 65-78.	0.7	41
153	A 92 GHz GaN HEMT voltage-controlled oscillator MMIC. , 2014, , .		14
154	Active harmonic source-/load-pull measurements of AlGaN/GaN HEMTs at X-band frequencies. , 2014, , .		6
155	X-band high-efficiency GaAs MMIC PA. , 2014, , .		3
156	Watt-level non-uniform distributed 6â€“37 GHz power amplifier MMIC with dual-gate driver stage in GaN technology. , 2014, , .		14
157	Growth model investigation for AlN/Al(Ga)InN interface growth by plasma-assisted molecular beam epitaxy for high electron mobility transistor applications. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2854-2860.	0.8	6
158	Q- and E-band amplifier MMICs for satellite communication. , 2014, , .		18
159	Comparison of second-harmonic matching of AlGaN/GaN HEMTs at K-band. , 2014, , .		2
160	Electroluminescence Investigation of the Lateral Field Distribution in AlGaN/GaN HEMTs for Power Applications. Acta Physica Polonica A, 2014, 125, 982-985.	0.2	3
161	Ultra-Wideband GaN MMIC Chip Set and High Power Amplifier Module for Multi-Function Defense AESA Applications. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 3043-3051.	2.9	52
162	High-Gain Millimeter-Wave AlGaN/GaN Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3112-3118.	1.6	16

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163	Novel semi-reactively-matched multistage broadband power amplifier architecture for monolithic ICs in GaN technology. , 2013, , .		8
164	Recent developments of Gallium Nitride monolithically-microwave integrated circuits for space. , 2013, , .		2
165	AlGaN/GaN-based variable gain amplifiers for W-band operation. , 2013, , .		1
166	Submicron-AlGaN/GaN MMICs for space applications. , 2013, , .		7
167	Guest Editorial Special Issue on GaN Electronic Devices. IEEE Transactions on Electron Devices, 2013, 60, 2975-2981.	1.6	11
168	Benchmarking of Large-Area GaN-on-Si HFET Power Devices for Highly-Efficient, Fast-Switching Converter Applications. , 2013, , .		9
169	New Low-Frequency Dispersion Model for AlGaN/GaN HEMTs Using Integral Transform and State Description. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 154-167.	2.9	23
170	GaNâ€based high voltage transistors for efficient power switching. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 831-834.	0.8	33
171	A 67 GHz GaN Voltage-Controlled Oscillator MMIC With High Output Power. IEEE Microwave and Wireless Components Letters, 2013, 23, 374-376.	2.0	16
172	GaN HEMTs and MMICs for space applications. Semiconductor Science and Technology, 2013, 28, 074010.	1.0	24
173	(In)AlGaN Heterojunction Field Effect Transistors and Circuits for High-Power Applications at Microwave and Millimeter-Wave Frequencies. Japanese Journal of Applied Physics, 2013, 52, 08JN13.	0.8	5
174	QFN-packaged highly-linear cascode GaN LNA MMIC from 0.5 to 3 GHz. , 2013, , .		5
175	Microscopic Degradation Analysis of RF-Stressed AlGaN/GaN HEMTs. Materials Science Forum, 2012, 725, 79-82.	0.3	2
176	Reverse bias stress test of GaN HEMTs for high-voltage switching applications. , 2012, , .		2
177	8â€“42 GHz GaN non-uniform distributed power amplifier MMICs in microstrip technology. , 2012, , .		13
178	Influence of AlGaN barrier thickness on electrical and device properties in Al0.14Ga0.86N/GaN high electron mobility transistor structures. Journal of Applied Physics, 2012, 112, .	1.1	7
179	A high-gain high-power amplifier MMIC for V-band applications using 100Ânm AlGaN/GaN dual-gate HEMTs. International Journal of Microwave and Wireless Technologies, 2012, 4, 267-274.	1.5	3
180	A U-band broadband power amplifier MMIC in 100 nm AlGaN/GaN HEMT technology. , 2012, , .		2

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181	Microwave and Millimeter Wave Integrated Circuits MTT-6: The RF Core Chips of the 21st Century [From the Guest Editors' Desk]. IEEE Microwave Magazine, 2012, 13, 24-141.	0.7	0
182	A high gain SiGe-GaN switching power amplifier in the GHz-range. , 2012, , .		3
183	Continuous-ClassF3 power amplifier mode varying simultaneously first 3 harmonic impedances. , 2012, , .		10
184	Generation of traps in AlGaN/GaN HEMTs during RF-and DC-stress test. , 2012, , .		27
185	Fractal structures for low-resistance large area AlGaN/GaN power transistors. , 2012, , .		5
186	AlGaN/GaN power amplifiers for ISM applications. Solid-State Electronics, 2012, 74, 108-113.	0.8	4
187	GaN-based millimeter-wave monolithic integrated circuits. , 2012, , .		0
188	The Continuous Inverse Class-F Mode With Resistive Second-Harmonic Impedance. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 1928-1936.	2.9	95
189	Radiative inter-valley transitions as a dominant emission mechanism in AlGaN/GaN high electron mobility transistors. Semiconductor Science and Technology, 2012, 27, 125003.	1.0	20
190	Dual-band Class-ABJ AlGaN/GaN high power amplifier. , 2012, , .		7
191	Tradeâ€offs between performance and reliability in AlGaN/GaN transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 365-368.	0.8	3
192	GaN-based high-frequency devices and circuits: A Fraunhofer perspective. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 491-496.	0.8	9
193	Development of 100 nm gate AlGaN/GaN HEMT and MMIC technology suitable for mmâ€wave applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 903-906.	0.8	19
194	Physics-Based Modeling of GaN HEMTs. IEEE Transactions on Electron Devices, 2012, 59, 685-693.	1.6	41
195	Reliability and degradation mechanism of 0.25 Âµm AlGaN/GaN HEMTs under RF stress conditions. , 2011, , .		5
196	Design and modelling challenges for advanced class-S digital transmitters. , 2011, , .		0
197	Dual-Gate GaN MMICs for MM-Wave Operation. IEEE Microwave and Wireless Components Letters, 2011, 21, 95-97.	2.0	20
198	A highly linear 84 GHz low noise amplifier MMIC in AlGaN/GaN HEMT technology. , 2011, , .		14

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199	Broadband GaN-Based Switch-Mode Core MMICs with 20 W Output Power Operating at UHF. , 2011, , .		7
200	A single-chip 77 GHz heterodyne receiver MMIC in 100 nm AlGaN/GaN HEMT technology. , 2011, , .		7
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